Update on the Common RD50 6" Project

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1) Wafers

n-type MCz: Zheng Li has a supply of n-type MCz (in addition to the p-type MCz). He will see how many he can supply.

FZ: the target for FZ should be about 1 kOhm for n-type and 3 kOhm for p-type

Thickness											
Wafer	bulk	#	[um]	SSD							
MCz	р	7	300	n-on-p							
DOFZ	р	5	300	n-on-p							
FZ	р	5	300	n-on-p							
MCz	n	3	300	p-on-n +n-on-n (no backside							
Fz	n	2	300	p-on-n +n-on-n (no backside							
MCz	n	3	200	p-on-n +n-on-n (no backside							

- 2) Details of strip detectors Use Width/pitch ~ 0.30 Combined P-stray [p-spray & p-stops] 4 um overhang on both sides (instead of 3) Guard rings: number: 6 distance 800um
- Layout on Wafer Common diodes with 4": 5 mm x 5 mm Common for 4" MPI test structures Many 1 cm test structures for technology, isolation tests

4) Common detector: one common detector between 4" and 6". To be replicated as often as space allows (3x for 6") to get enough detectors for testing.

		# of		# of	Len							
Inst.	Device	dev.	Footprint	Pitch	strips	gth	Metal	Bias	Coupling	Isolation	w/p	p-implant
4"	Short strips	1	3.1 x 1.2	80	128	3	single	poly 1M	AC	Comb p	0.3	3 24

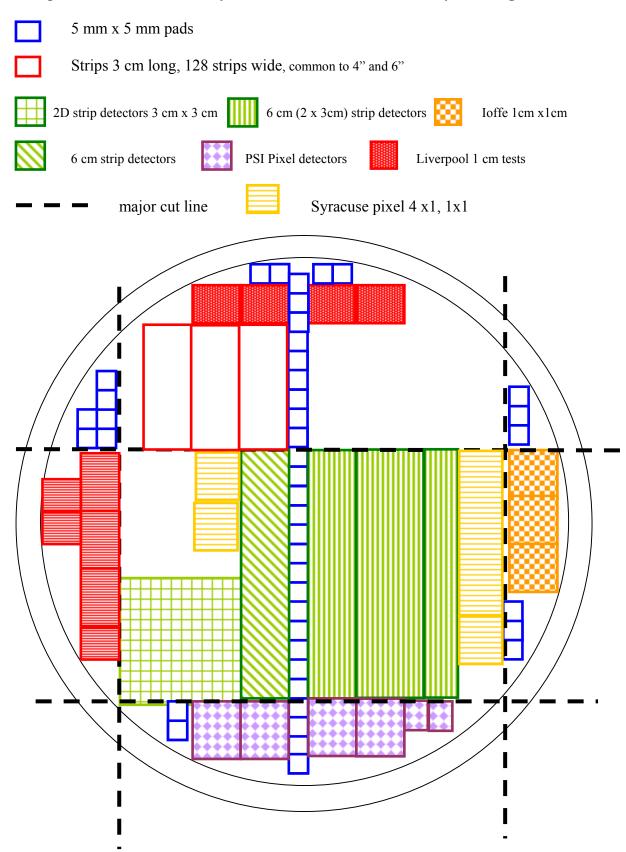
5) UCSC structures (changes in red)

Inst.	Device	# of dev.	Footprint	-	# of strips	Len gth Metal	Bias	Coupling	Isolation	w/p	p-implant
UCSC	Short strips	1	6.2 x 0.80	50	128	2 x 3 Single	poly 1M	AC	Mod p	0.3	10
UCSC	Short strips	1	6.2 x 1.2	80	128	2 x 3 Single	poly 1M	AC	Mod p	0.3	30
UCSC	Short strips	1	6.2 x 1.5	100	128	2 x 3 Single	poly 1M	AC	Mod p	0.3	30
UCSC	Medium strips	1	6.2 x 1.2	80	128	6 Single	poly 1M	AC	Mod p	0.3	25
6)	Pixel structur	es:									

6) Pixel structures: Are the Syracuse detectors identical to what Tilman proposes?

Updated List of SSD and Pads (much space to be filled with duplicates)

Inot	Device	# of	Footprint		# of	Len gth	Motol	Pice	Coupling	Isolation	w/n	n implant
Inst.	Device	uev.	Footprint		•	gui	Metal	Bias	Coupling		•	p-implant
UCSC	Short strips	1	6.2 x 0.80	50	128	2 x 3	3 Single	poly 1M	AC	Mod p	0.3	3 10
UCSC	Short strips	1	6.2 x 1.2	80	128	2 x 3	3 Single	poly 1M	AC	Mod p	0.3	30
UCSC	Short strips	1	6.2 x 1.5	100	128	2 x 3	3 Single	poly 1M	AC	Mod p	0.3	30
UCSC	Medium strips	1	6.2 x 1.2	80	128	6	Single	poly 1M	AC	Mod p	0.3	3 25
BNL	2-D	1	3.2 x 3	50	256	6	Single		DC	p-spray	0.6	6
loffe	very short strips	3	1.2 x 1.2	100	64	~1		poly 1M	AC and DC	Mod p		
PSI etc	Pixel 1	2	1.04 x 0.98							Mod p		
PSI etc	Pixel 2	2	1.02 x 0.99							Mod p		
PSI etc	Pixel 3	2	0.62 x 0.54							Mod p		
Liverpool	Test structures	3	1 x 0.8	50	128	1	Single	poly 1M	AC	All?		
Liverpool	Test structures	4	1 x 1.2	80	128	1	Single	poly 1M	AC	All?		
Liverpool	Test structures	3	1 x 1.5	100	128	1	Single	poly 1M	AC	All?		
Syracuse	Pixel1x4	1	0.85x3.93	50	22x128x4		Single		dc	mod p		28um (n+ implant) 28um(n+
Syracuse	Pixel 1x1	3	0.85X1.14	50	22x128		Single		dc	Mod p		implant)
4"	Short strips	1	3.1 x 1.2	80	128	3	single	poly 1M	AC	Comnb p	0.3	3 24



Proposed 6" Wafer Mask Layout with free areas to be filled by Gianluigi